# **VP0550**

# P-Channel Enhancement-Mode Vertical DMOS FET

#### **Features**

- · Free from Secondary Breakdown
- · Low Power Drive Requirement
- · Ease of Paralleling
- Low C<sub>ISS</sub> and Fast Switching Speeds
- · Excellent Thermal Stability
- · Integral Source-to-Drain Diode
- · High Input Impedance and High Gain

#### **Applications**

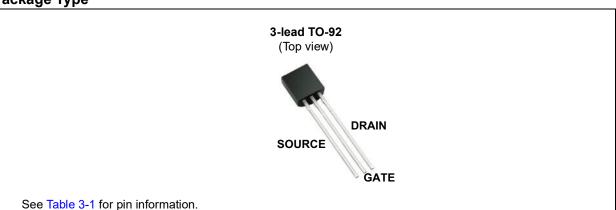
- · Motor Controls
- · Converters, Amplifiers and Switches
- · Power Supply Circuits
- Drivers (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

#### **General Description**

The VP0550 low-threshold, Enhancement-mode (normally-off) transistor uses a vertical DMOS structure and a well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally induced secondary breakdown.

Microchip's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where very low threshold voltage, high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

#### **Package Type**



#### 1.0 ELECTRICAL CHARACTERISTICS

#### **Absolute Maximum Ratings†**

Drain-to-Source Voltage	BV <sub>DSS</sub>
Drain-to-Gate Voltage	
Gate-to-Source Voltage	200
Operating Ambient Temperature, T <sub>A</sub>	
Storage Temperature, T <sub>S</sub>	

**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

### DC ELECTRICAL CHARACTERISTICS

**Electrical Specifications:**  $T_A = 25^{\circ}$ C unless otherwise specified. All DC parameters are 100% tested at 25°C unless otherwise stated. Pulse test: 300 µs pulse, 2% duty cycle

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions		
Drain-to-Source Breakdown Voltage	BV <sub>DSS</sub>	-500	_		V	$V_{GS} = 0V$ , $I_D = -1$ mA		
Gate Threshold Voltage	V <sub>GS(th)</sub>	-2		-4.5	V	$V_{GS} = V_{DS}$ , $I_D = -1$ mA		
Change in V <sub>GS(th)</sub> with Temperature	$\Delta V_{GS(th)}$		3.5	6	mV/°C	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -1 mA ( <b>Note 1</b> )		
Gate Body Leakage Current	I <sub>GSS</sub>		_	-100	nA	$V_{GS}$ = ±20V, $V_{DS}$ = 0V		
				-10	μA	V <sub>GS</sub> = 0V, V <sub>DS</sub> = Maximum rating		
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	l	l	-1000	μA	$V_{DS}$ = 0.8 Maximum rating, $V_{GS}$ = 0V, $T_A$ = 125°C (Note 1)		
On-State Drain Current	1		<b>-90</b>		mA	$V_{GS} = -5V, V_{DS} = -25V$		
On-State Drain Gunent	I <sub>D(ON)</sub>	-100	-240		mA	$V_{GS} = -10V, V_{DS} = -25V$		
Static Drain-to-Source On-State Resistance	D	l	85		Ω	$V_{GS} = -5V, I_{D} = -5 \text{ mA}$		
Static Diam-to-Source On-State Resistance	R <sub>DS(ON)</sub>		80	125	Ω	$V_{GS} = -10V, I_{D} = -10 \text{ mA}$		
Change in R <sub>DS(ON)</sub> with Temperature	$\Delta R_{DS(ON)}$		0.85	_	%/°C	$V_{GS} = -10V, I_{D} = -10 \text{ mA}$ (Note 1)		

**Note 1:** Specification is obtained by characterization and is not 100% tested.

# **AC ELECTRICAL CHARACTERISTICS**

<b>Electrical Specifications:</b> $T_A = 25$ °C unless otherwise specified. All AC parameters are not 100% sample tested.								
Parameter		Min.	Тур.	Max.	Unit	Conditions		
Forward Transconductance	G <sub>FS</sub>	25	40	_	mmho	$V_{DS} = -25V$ , $I_{D} = -10$ mA		
Input Capacitance	C <sub>ISS</sub>	_	40	70	pF	$V_{GS} = 0V$ ,		
Common-Source Output Capacitance	Coss	_	10	20	pF	$V_{DS} = -25V$ ,		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	3	10	pF	f = 1 MHz		
Turn-On Delay Time	t <sub>d(ON)</sub>	_	5	10	ns			
Rise Time	t <sub>r</sub>	_	8	10	ns	$V_{DD} = -25V$ ,		
Turn-Off Delay Time		_	8	15	ns	$I_D = -100 \text{ mA},$ $R_{GEN} = 25\Omega$		
Fall Time	t <sub>f</sub>	_	5	16	ns	GLIN		
DIODE PARAMETER								
Diode Forward Voltage Drop	V <sub>SD</sub>	_	-0.8	-1.5	V	V <sub>GS</sub> = 0V, I <sub>SD</sub> = -0.1A ( <b>Note 1</b> )		
Reverse Recovery Time	t <sub>rr</sub>	_	200	_	ns	$V_{GS} = 0V, I_{SD} = -0.1A$		

**Note 1:** Unless otherwise stated, all DC parameters are 100% tested at 25°C. Pulse test: 300 μs pulse, 2% duty cycle

#### **TEMPERATURE SPECIFICATIONS**

Parameter	Sym.	Min.	Тур.	Max.	Unit	Conditions	
TEMPERATURE RANGE							
Operating Ambient Temperature	T <sub>A</sub>	-55	_	+150	°C		
Storage Temperature	T <sub>S</sub>	-55	_	+150	°C		
PACKAGE THERMAL RESISTANCE							
3-lead TO-92	$\theta_{JA}$	_	132	_	°C/W		

#### THERMAL CHARACTERISTICS

Package	I <sub>D</sub> (Note 1) (Continuous) (mA)	I <sub>D</sub> (Pulsed) (mA)	Power Dissipation at T <sub>A</sub> = 25°C (W)	I <sub>DR</sub> (Note 1) (mA)	I <sub>DRM</sub> (mA)
3-lead TO-92	-54	-250	1	-54	-250

**Note 1:**  $I_D$  (continuous) is limited by maximum rated  $T_J$ .

#### 2.0 TYPICAL PERFORMANCE CURVES

**Note:** The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g. outside specified power supply range) and therefore outside the warranted range.

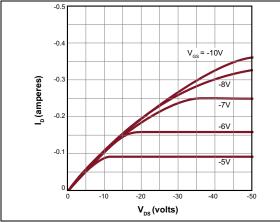
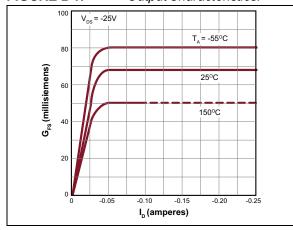
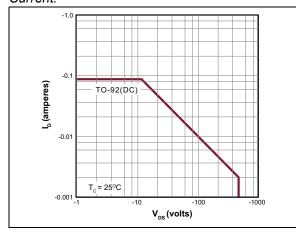


FIGURE 2-1: Output Characteristics.



**FIGURE 2-2:** Transconductance vs. Drain Current.



**FIGURE 2-3:** Maximum Rated Safe Operating Area.

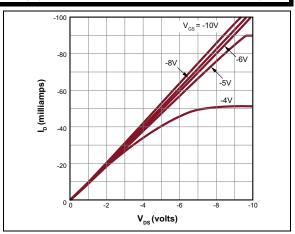
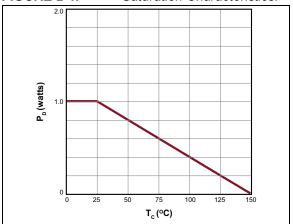
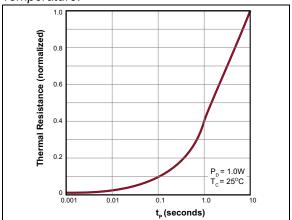


FIGURE 2-4: Saturation Characteristics.



**FIGURE 2-5:** Power Dissipation vs. Case Temperature.



**FIGURE 2-6:** Thermal Response Characteristics.

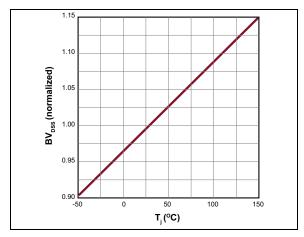


FIGURE 2-7: Temperature.

 $BV_{DSS}$  Variation with

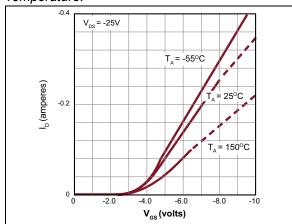
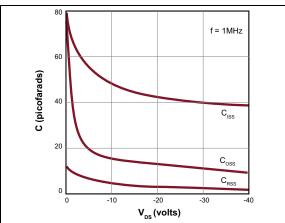


FIGURE 2-8: Transfer Characteristics.

Transier Characteristics



**FIGURE 2-9:** Capacitance vs. Drain-to-Source Voltage.

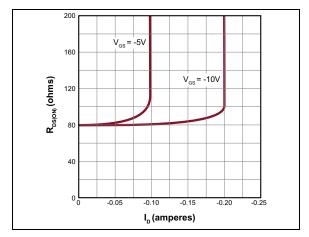


FIGURE 2-10:

On-Resistance vs. Drain

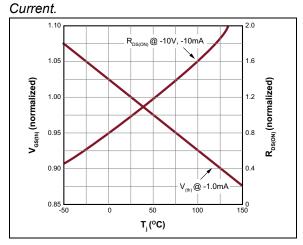


FIGURE 2-11:

 $V_{(th)}$  and  $R_{DS}$  Variation with

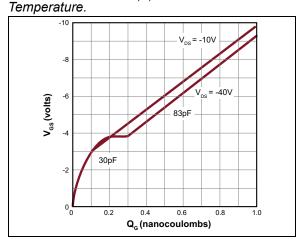


FIGURE 2-12: Characteristics.

Gate Drive Dynamic

#### 3.0 PIN DESCRIPTION

The details on the pins of VP0550 are listed in Table 3-1. Refer to **Package Type** for the location of pins.

TABLE 3-1: PIN FUNCTION TABLE

Pin Number	Pin Name	Description						
1	Source	Source						
2	Gate	Gate						
3	Drain	Drain						

#### 4.0 FUNCTIONAL DESCRIPTION

Figure 4-1 illustrates the switching waveforms and test circuit for VP0550.

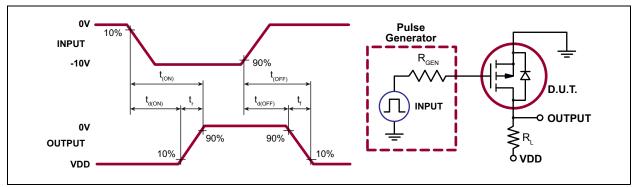


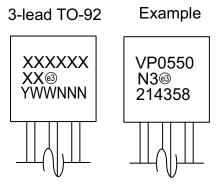
FIGURE 4-1: Switching Waveforms and Test Circuit.

TABLE 4-1: PRODUCT SUMMARY

BV <sub>DSS</sub> /BV <sub>DGS</sub> (V)	R <sub>DS(ON)</sub> (Maximum) (Ω)	I <sub>D(ON)</sub> (Minimum) (mA)
-500	125	-100

#### 5.0 PACKAGING INFORMATION

## 5.1 Package Marking Information



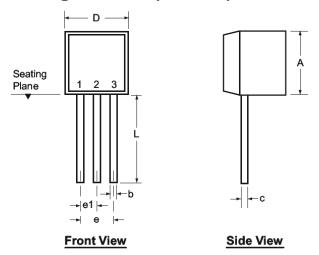
Legend: XX...X Product Code or Customer-specific information
Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')
NNN Alphanumeric traceability code

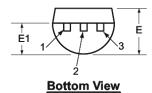
© Pb-free JEDEC® designator for Matte Tin (Sn)

\* This package is Pb-free. The Pb-free JEDEC designator (©3)
can be found on the outer packaging for this package.

**Note**: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for product code or customer-specific information. Package may or not include the corporate logo.

# 3-Lead TO-92 Package Outline (L/LL/N3)





Note: For the most current package drawings, see the Microchip Packaging Specification at www.microchip.com/packaging.

Symb	ol	Α	b	С	D	Е	E1	е	e1	L
	MIN	.170	.014 <sup>†</sup>	.014 <sup>†</sup>	.175	.125	.080	.095	.045	.500
Dimensions (inches)	NOM	-	-	-	-	-	-	-	-	-
(51100)	MAX	.210	.022 <sup>†</sup>	.022†	.205	.165	.105	.105	.055	.610*

Drawings not to scale.

JEDEC Registration TO-92.
\* This dimension is not specified in the JEDEC drawing.
† This dimension differs from the JEDEC drawing.



NOTES:

#### APPENDIX A: REVISION HISTORY

#### Revision A (April 2022)

- Converted Supertex Doc# DSFP-VP0550 to Microchip DS20006003A
- Changed the package marking format
- Removed the 3-lead TO-92 N3 P002, P003, P005, and P014 media types to align packaging specifi-cations with the actual BQM
- Added some sections to comply with the standard Microchip format
- Made minor text changes throughout the document

# PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

PART NO.	<u> </u>	- <b>x</b> - <b>x</b>	Examples:
Device	Packaç Option		a) VP0550N3-G: P-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 1000/Bag
Device:	VP0550	P-Channel Enhancement-Mode Vertical DMOS FET	b) VP0550N3-G-P013: P-Channel Enhancement- Mode, Vertical DMOS FET, 3-lead TO-92, 2000/AMMO Pack
Package:	N3	3-lead TO-92	rack
Environmental:	G	Lead (Pb)-free/RoHS-compliant Package	
Media Types:	,	1000/Bag for an N3 Package 2000/AMMO Pack for an N3 Package	

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